

N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

Rev. 2 — 2 March 2012

**Product data sheet** 

### 1. Product profile

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#### 1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	92	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	149	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 13</u> ; see <u>Figure 9</u>	-	5.9	7.8	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 30 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	10.6	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 30 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	38.7	-	nC
Avalanch	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \ I_{D} = 92 \ A; \\ V_{sup} \leq 100 \ V; \ R_{GS} = 50 \ \Omega; \ unclamped \end{array}$	-	-	110	mJ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

## 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R6-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

#### Table 4. Limiting values

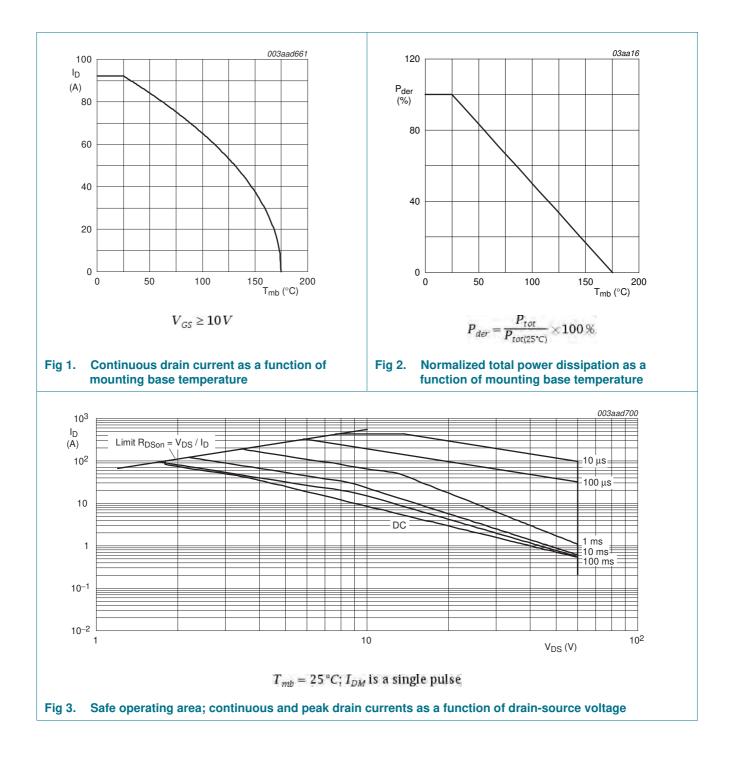
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>i</sub> ≥ 25 °C; T <sub>i</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
ID	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	65	Α
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	92	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>	-	389	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	149	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
ls	source current	T <sub>mb</sub> = 25 °C	-	92	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	389	А
Avalanche ru	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 92 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	110	mJ

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#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

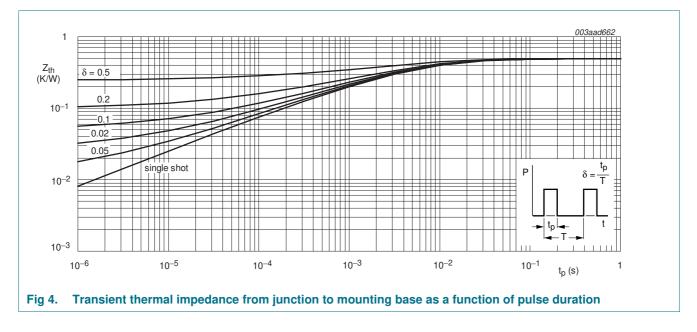


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#### N-channel 60 V 7.8 m $\Omega$ standard level MOSFET in D2PAK

### 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.49	1.01	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

## 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 11	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 11</u>	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^\circ C$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	13.3	18	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u> ; see <u>Figure 9</u>	-	5.9	7.8	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.98	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	38.7	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	12.9	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	6.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	6	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 15</u> ; see <u>Figure 14</u>	-	10.6	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	5.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; see <u>Figure 16</u> ; see <u>Figure 8</u>	-	2651	-	pF
C <sub>oss</sub>	output capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	342	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; see <u>Figure 16</u> ; see <u>Figure 8</u>	-	183	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	19	-	ns
r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	21	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	37	-	ns
t <sub>f</sub>	fall time		-	13	-	ns

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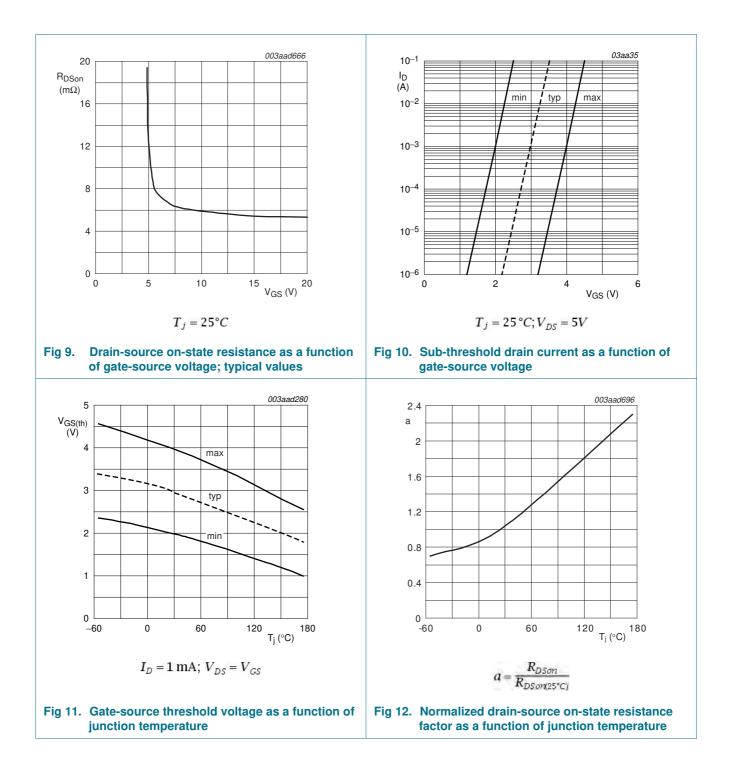
Symbol I	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain die	ode					
/ <sub>SD</sub> s	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	0.86	1.2	V
r <b>r</b>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	40.4	-	ns
ک <sub>r</sub> r	recovered charge	V <sub>DS</sub> = 30 V	-	56	-	nC
(A) 1 (A) 80 60 40 20 0 0	$\begin{array}{c} 15 \\ 10 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ 0 \\ $	urrent as a	40 60	80	<sup>203aad669</sup>	n of
100 I <sub>D</sub> (A) 80 60		003aad665 4000 C (pF) 3000			003aad664	
		2000 Crss				
40 20	T <sub>j</sub> = 175 °C	T <sub>j</sub> = 25 °C 1000				
	$T_{j} = 175 \text{ °C}$ $2  4$ $V_{DS} = 25 \text{ V}$	V <sub>GS</sub> (V) 6 0 0 5	10			

#### Table 6. Characteristics ...continued

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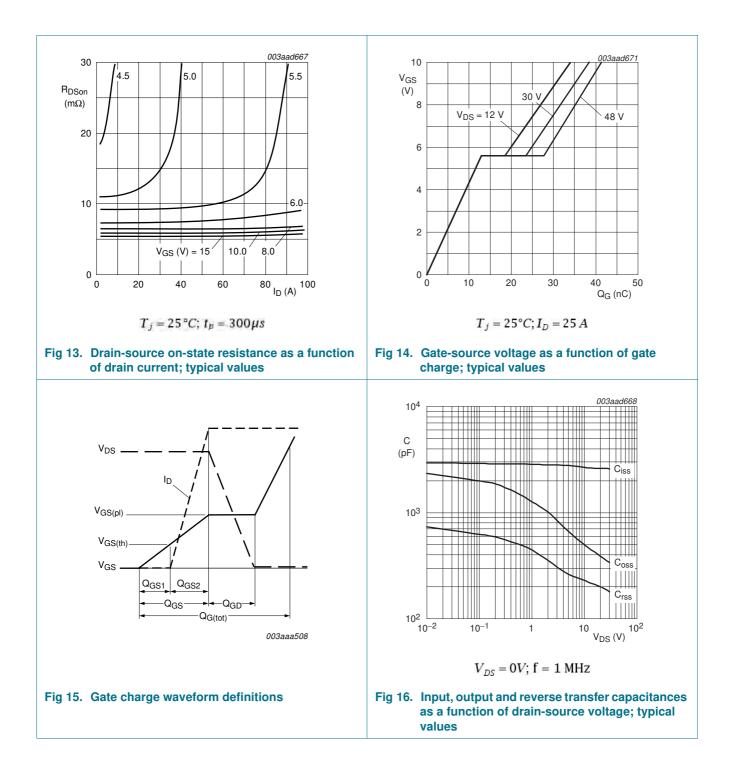
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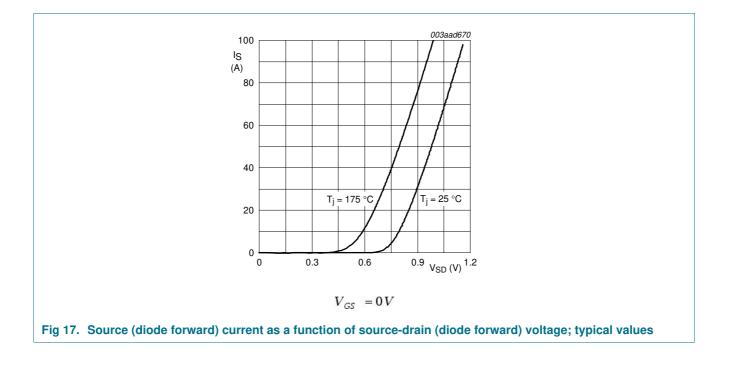
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#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK



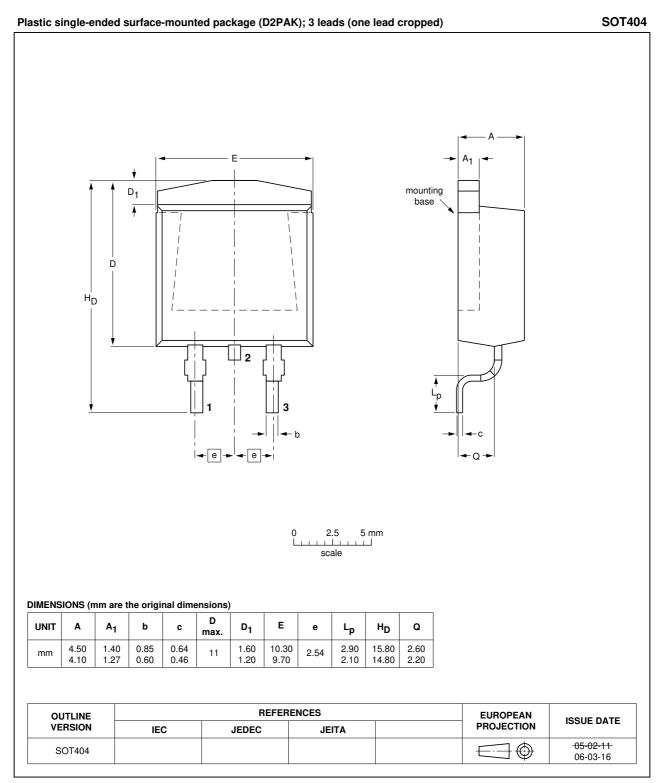
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#### N-channel 60 V 7.8 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

### 7. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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#### N-channel 60 V 7.8 mΩ standard level MOSFET in D2PAK

### 8. Revision history

#### Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R6-60BS v.2	20120302	Product data sheet	-	PSMN7R6-60BS v.1
Modifications:	<ul><li>Status changed fr</li><li>Various changes fr</li></ul>	om objective to product. to content.		
PSMN7R6-60BS v.1	20111020	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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